

No.4644

2SA1857

PNP Epitaxial Planar Silicon Transistor FM, RF, MIX, IF Amp, High-Frequency General-Purpose Amp Applications

Features

- + High power gain : PG = 25dB typ (f = 100MHz)
- · High cutoff frequency: f_T=750MHz typ.
- · Low collector to emitter saturation voltage.
- · Complementary pair with the 2SC4400.

Absolute Maximum Ratings at Ta = 25°	ue maximum naungsat ia=za t
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6	
Collector to Base Voltage	$\rm V_{CBO}$
Collector to Emitter Voltage	$\rm v_{ceo}$
Emitter to Base Voltage	$ m V_{EBO}$
Collector Current	${ m I}_{ m C}$
Collector Dissipation	$P_{\mathbf{C}}$
Junction Temperature	$\mathbf{T}\mathbf{j}$
Storage Temperature	Tstg

-15	V
-12	V
-3	V
- 50	mA
150	mW
150	$^{\circ}\mathrm{C}$
3 - 55 to + 150	$^{\circ}\mathrm{C}$
1 1	
min typ	max

unit

Electrical Characteristics at Ta = 25°C

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Collector Cutoff Current	I_{CBO}
Emitter Cutoff Current	I_{EBO}
DC Current Gain	h_{FE}
Gain-Bandwidth Product	$\mathbf{f_T}$
Output Capacitance	Cob
Reverse Transfer Capacitance	Cre
C-E Saturation Voltage	VCE
Power Gain	PG

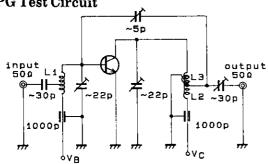
3. 34	min	typ	max	unit
$V_{CB} = -12V, I_E = 0$			-0.1	μ A
$V_{EB} = -2V, I_C = 0$			-0.1	μ A
$V_{\rm CE} = -10 \rm V, I_{\rm C} = -5 mA$	60×		270%	•
$V_{CE} = -10V, I_{C} = -5mA$		750		MHz
$V_{CB} = -10V$, $f = 1MHz$		1.2	1.6	pF
$V_{CB} = -10V$, $f = 1MHz$		0.9		\mathbf{pF}
$I_C = -10 \text{mA}, I_B = -1 \text{mA}$	_	- 0.1	-0.3	V
$V_{CE} = -10V, I_{C} = -10mA,$		25		dB
f = 100MHz				

* The 2SA1857 is classified by 5mA hFE as follows:

60 3 120	90 4 180	135 5 270

Marking: JS h_{FE} rank: 3, 4, 5

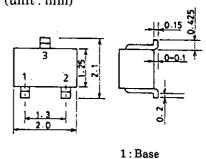
PG Test Circuit



Unit (Capacitance: F) A01661

- L1: $1 \text{mm} \phi$ plated wire $10 \text{mm} \phi$ 5T, pitch 15mm, tap: 2T from base side
- L2: $1mm\phi$ plated wire $10mm\phi$ 7T, pitch 10mm, tap: 2T from V_C side
- L3:1mm ø enamel wire 10mm ø 3T, pitch 10mm

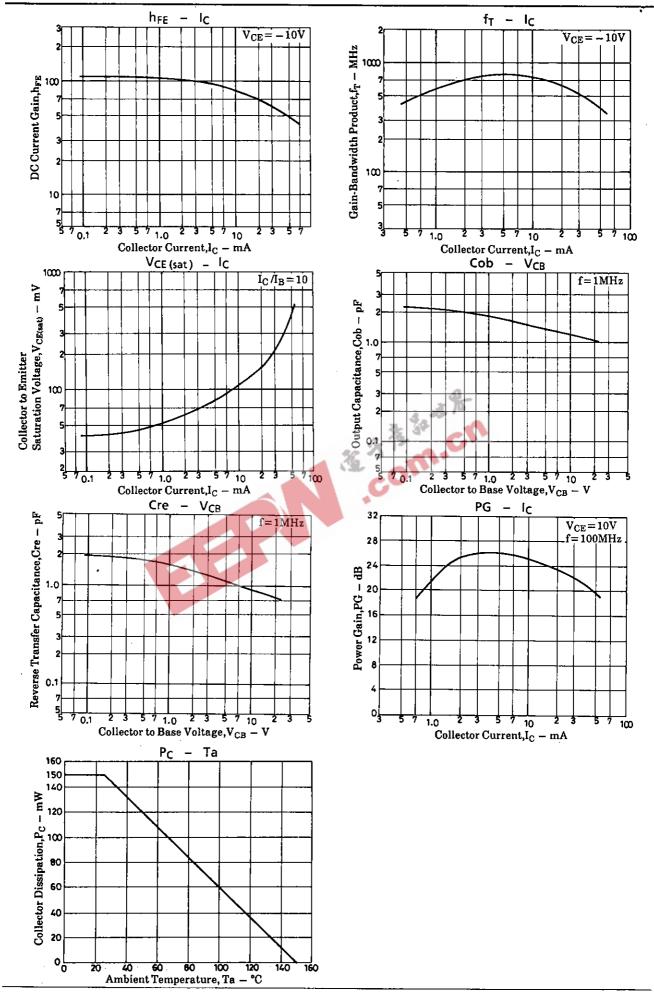
Package Dimensions 2059A (unit: mm)





2: Emitter 3: Collector

SANYO: MCP





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